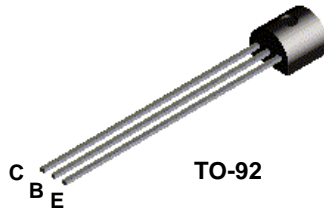
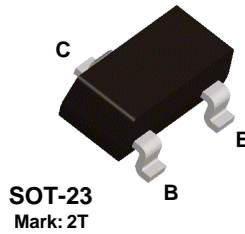


**2N4403**



**MMBT4403**



**PNP General Purpose Amplifier**

This device is designed for use as a general purpose amplifier and switch requiring collector currents to 500 mA. Sourced from Process 63. See PN2907A for characteristics.

**Absolute Maximum Ratings\*** TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V <sub>CEO</sub>	Collector-Emitter Voltage	40	V
V <sub>CBO</sub>	Collector-Base Voltage	45	V
V <sub>EBO</sub>	Emitter-Base Voltage	5.0	V
I <sub>C</sub>	Collector Current - Continuous	800	mA
T <sub>J</sub> , T <sub>stg</sub>	Operating and Storage Junction Temperature Range	-55 to +150	°C

\*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

**NOTES:**

- 1) These ratings are based on a maximum junction temperature of 150 degrees C.
- 2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

**Thermal Characteristics** TA = 25°C unless otherwise noted

Symbol	Characteristic	Max		Units
		2N4403	*MMBT4403	
P <sub>D</sub>	Total Device Dissipation Derate above 25°C	625	350	mW
		5.0	2.8	mW/°C
R <sub>θJC</sub>	Thermal Resistance, Junction to Case	83.3		°C/W
R <sub>θJA</sub>	Thermal Resistance, Junction to Ambient	200	357	°C/W

\*Device mounted on FR-4 PCB 1.6" X 1.6" X 0.06."

# PNP General Purpose Amplifier

(continued)

## Electrical Characteristics

TA = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Max	Units
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### OFF CHARACTERISTICS

$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage*	$I_C = 1.0 \text{ mA}, I_B = 0$	40		V
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	$I_C = 0.1 \text{ mA}, I_E = 0$	45		V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	$I_E = 0.1 \text{ A}, I_C = 0$	5.0		V
$I_{BEX}$	Base Cutoff Current	$V_{CE} = 35 \text{ V}, V_{EB} = 0.4 \text{ V}$		0.1	$\mu\text{A}$
$I_{CEX}$	Collector Cutoff Current	$V_{CE} = 35 \text{ V}, V_{BE} = 0.4 \text{ V}$		0.1	$\mu\text{A}$

### ON CHARACTERISTICS

$h_{FE}$	DC Current Gain	$I_C = 0.1 \text{ mA}, V_{CE} = 1.0 \text{ V}$ $I_C = 1.0 \text{ mA}, V_{CE} = 1.0 \text{ V}$ $I_C = 10 \text{ mA}, V_{CE} = 1.0 \text{ V}$ $I_C = 150 \text{ mA}, V_{CE} = 2.0 \text{ V}^*$ $I_C = 500 \text{ mA}, V_{CE} = 2.0 \text{ V}^*$	30 60 100 100 20	300	
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage*	$I_C = 150 \text{ mA}, I_B = 15 \text{ mA}$ $I_C = 500 \text{ mA}, I_B = 50 \text{ mA}$		0.4 0.75	V V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C = 150 \text{ mA}, I_B = 15 \text{ mA}^*$ $I_C = 500 \text{ mA}, I_B = 50 \text{ mA}$	0.75	0.95 1.3	V V

### SMALL SIGNAL CHARACTERISTICS

$f_T$	Current Gain - Bandwidth Product	$I_C = 20 \text{ mA}, V_{CE} = 10 \text{ V},$ $f = 100 \text{ MHz}$	200		MHz
$C_{cb}$	Collector-Base Capacitance	$V_{CB} = 10 \text{ V}, I_E = 0,$ $f = 140 \text{ kHz}$		8.5	pF
$C_{eb}$	Emitter-Base Capacitance	$V_{BE} = 0.5 \text{ V}, I_C = 0,$ $f = 140 \text{ kHz}$		30	pF
$h_{ie}$	Input Impedance	$I_C = 1.0 \text{ mA}, V_{CE} = 10 \text{ V},$ $f = 1.0 \text{ kHz}$	1.5	15	$k\Omega$
$h_{re}$	Voltage Feedback Ratio	$I_C = 1.0 \text{ mA}, V_{CE} = 10 \text{ V},$ $f = 1.0 \text{ kHz}$	0.1	8.0	$\times 10^{-4}$
$h_{fe}$	Small-Signal Current Gain	$I_C = 1.0 \text{ mA}, V_{CE} = 10 \text{ V},$ $f = 1.0 \text{ kHz}$	60	500	
$h_{oe}$	Output Admittance	$I_C = 1.0 \text{ mA}, V_{CE} = 10 \text{ V},$ $f = 1.0 \text{ kHz}$	1.0	100	$\mu\text{mhos}$

### SWITCHING CHARACTERISTICS

$t_d$	Delay Time	$V_{CC} = 30 \text{ V}, I_C = 150 \text{ mA},$		15	ns
$t_r$	Rise Time	$I_{B1} = 15 \text{ mA}$		20	ns
$t_s$	Storage Time	$V_{CC} = 6.0 \text{ V}, I_C = 150 \text{ mA}$		225	ns
$t_f$	Fall Time	$I_{B1} = I_{B2} = 15 \text{ mA}$		30	ns

\*Pulse Test: Pulse Width  $\leq 300 \mu\text{s}$ , Duty Cycle  $\leq 2.0\%$

2N4403 / MMBT4403